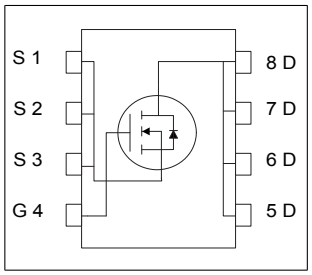
# MOSFET

## OptiMOS™ Power-MOSFET, 25 V

TSDSON-8 FL (S3O8)

### Features

- Optimized for high performance Buck converter (Server,VGA)
- Very Low $FOM_{QOSS}$ for High Frequency SMPS
- Low $FOM_{SW}$ for High Frequency SMPS
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}$=4.5 V
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21




### Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|---|---|---|
| $V_{DS}$ | 25 | V |
| $R_{DS(on),max}$@$V_{GS}$=10 V | 1.8 | mΩ |
| $R_{DS(on),max}$@$V_{GS}$=4.5 V | 2.4 | mΩ |
| $I_D$ | 153 | A |

| Type / Ordering Code | Package | Marking | Related Links |
|---|---|---|---|
| BSZ018NE2LS | PG-TSDSON-8 FL | 018NE2L | - |

[1] J-STD20 and JESD22

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# 1 Maximum ratings

at $T_A$=25 °C, unless otherwise specified

## Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Continuous drain current[1] | $I_D$ | -<br>-<br>-<br>-<br>- | -<br>-<br>-<br>-<br>- | 153<br>97<br>133<br>84<br>23 | A | $V_{GS}$=10 V, $T_C$=25 °C<br>$V_{GS}$=10 V, $T_C$=100 °C<br>$V_{GS}$=4.5 V, $T_C$=25 °C<br>$V_{GS}$=4.5 V, $T_C$=100 °C<br>$V_{GS}$=4.5 V, $T_A$=25 °C, $R_{thJA}$=60 K/W |
| Pulsed drain current[2] | $I_{D,pulse}$ | - | - | 612 | A | $T_C$=25 °C |
| Avalanche current, single pulse[3] | $I_{AS}$ | - | - | 20 | A | $T_C$=25 °C |
| Avalanche energy, single pulse | $E_{AS}$ | - | - | 150 | mJ | $I_D$=20 A, $R_{GS}$=25 Ω |
| Gate source voltage | $V_{GS}$ | -20 | - | 20 | V | - |
| Power dissipation | $P_{tot}$ | -<br>- | -<br>- | 69<br>2.1 | W | $T_C$=25 °C<br>$T_A$=25 °C, $R_{thJA}$=60 K/W |
| Operating and storage temperature | $T_j$, $T_{stg}$ | -55 | - | 150 | °C | IEC climatic category;<br>DIN IEC 68-1: 55/150/56 |

# 2 Thermal characteristics

## Table 3 Thermal characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | $R_{thJC}$ | - | - | 1.8 | K/W | - |
| Device on PCB,<br>6 cm² cooling area[4] | $R_{thJA}$ | - | - | 60 | K/W | - |

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] See Diagram 3 for more detailed information
[3] See Diagram 13 for more detailed information
[4] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

# 3 Electrical characteristics

at $T_j$=25 °C, unless otherwise specified

## Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 25 | - | - | V | $V_{GS}$=0 V, $I_D$=1 mA |
| Gate threshold voltage | $V_{GS(th)}$ | 1.2 | - | 2 | V | $V_{DS}$=$V_{GS}$, $I_D$=250 µA |
| Zero gate voltage drain current | $I_{DSS}$ | -<br>- | 0.1<br>10 | 1<br>100 | µA | $V_{DS}$=25 V, $V_{GS}$=0 V, $T_j$=25 °C<br>$V_{DS}$=25 V, $V_{GS}$=0 V, $T_j$=125 °C |
| Gate-source leakage current | $I_{GSS}$ | - | 10 | 100 | nA | $V_{GS}$=20 V, $V_{DS}$=0 V |
| Drain-source on-state resistance | $R_{DS(on)}$ | -<br>- | 1.9<br>1.5 | 2.4<br>1.8 | mΩ | $V_{GS}$=4.5 V, $I_D$=30 A<br>$V_{GS}$=10 V, $I_D$=30 A |
| Gate resistance | $R_G$ | 0.4 | 0.8 | 1.6 | Ω | - |
| Transconductance | $g_{fs}$ | 70 | 140 | - | S | $\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, $I_D$=30 A |

## Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Input capacitance[1)] | $C_{iss}$ | - | 2800 | 3724 | pF | $V_{GS}$=0 V, $V_{DS}$=12 V, $f$=1 MHz |
| Output capacitance[1)] | $C_{oss}$ | - | 1000 | 1330 | pF | $V_{GS}$=0 V, $V_{DS}$=12 V, $f$=1 MHz |
| Reverse transfer capacitance | $C_{rss}$ | - | 110 | - | pF | $V_{GS}$=0 V, $V_{DS}$=12 V, $f$=1 MHz |
| Turn-on delay time | $t_{d(on)}$ | - | 5.5 | - | ns | $V_{DD}$=12 V, $V_{GS}$=10 V, $I_D$=30 A, $R_{G,ext}$=1.6 Ω |
| Rise time | $t_r$ | - | 4.4 | - | ns | $V_{DD}$=12 V, $V_{GS}$=10 V, $I_D$=30 A, $R_{G,ext}$=1.6 Ω |
| Turn-off delay time | $t_{d(off)}$ | - | 26 | - | ns | $V_{DD}$=12 V, $V_{GS}$=10 V, $I_D$=30 A, $R_{G,ext}$=1.6 Ω |
| Fall time | $t_f$ | - | 3.4 | - | ns | $V_{DD}$=12 V, $V_{GS}$=10 V, $I_D$=30 A, $R_{G,ext}$=1.6 Ω |

## Table 6 Gate charge characteristics[2)]

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Gate to source charge[1)] | $Q_{gs}$ | - | 7.0 | 9.3 | nC | $V_{DD}$=12 V, $I_D$=30 A, $V_{GS}$=0 to 4.5 V |
| Gate charge at threshold | $Q_{g(th)}$ | - | 4.5 | - | nC | $V_{DD}$=12 V, $I_D$=30 A, $V_{GS}$=0 to 4.5 V |
| Gate to drain charge[1)] | $Q_{gd}$ | - | 4.3 | 6.5 | nC | $V_{DD}$=12 V, $I_D$=30 A, $V_{GS}$=0 to 4.5 V |
| Switching charge | $Q_{sw}$ | - | 6.7 | - | nC | $V_{DD}$=12 V, $I_D$=30 A, $V_{GS}$=0 to 4.5 V |
| Gate charge total[1)] | $Q_g$ | - | 18.6 | 25 | nC | $V_{DD}$=12 V, $I_D$=30 A, $V_{GS}$=0 to 4.5 V |
| Gate plateau voltage | $V_{plateau}$ | - | 2.5 | - | V | $V_{DD}$=12 V, $I_D$=30 A, $V_{GS}$=0 to 4.5 V |
| Gate charge total[1)] | $Q_g$ | - | 39 | 52 | nC | $V_{DD}$=12 V, $I_D$=30 A, $V_{GS}$=0 to 10 V |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | - | 16.2 | - | nC | $V_{DS}$=0.1 V, $V_{GS}$=0 to 4.5 V |
| Output charge[1)] | $Q_{oss}$ | - | 21 | 28 | nC | $V_{DD}$=12 V, $V_{GS}$=0 V |

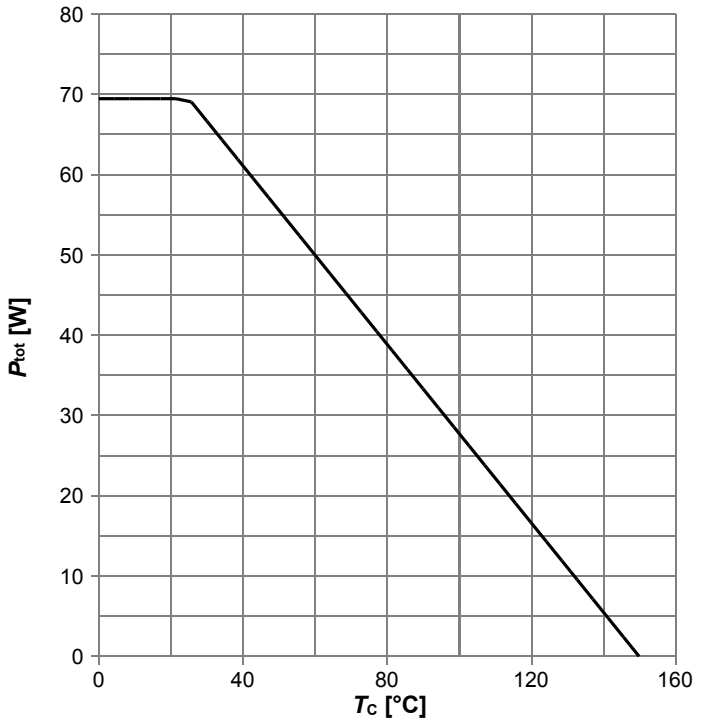
[1)] Defined by design. Not subject to production test
[2)] See "Gate charge waveforms" for parameter definition

## Table 7 Reverse diode

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Diode continuous forward current | $I_S$ | - | - | 63 | A | $T_C$=25 °C |
| Diode pulse current | $I_{S,pulse}$ | - | - | 612 | A | $T_C$=25 °C |
| Diode forward voltage | $V_{SD}$ | - | 0.8 | 1 | V | $V_{GS}$=0 V, $I_F$=20 A, $T_j$=25 °C |
| Reverse recovery charge | $Q_{rr}$ | - | 20 | - | nC | $V_R$=15 V, $I_F$=$I_S$, d$i_F$/d$t$=400 A/µs |

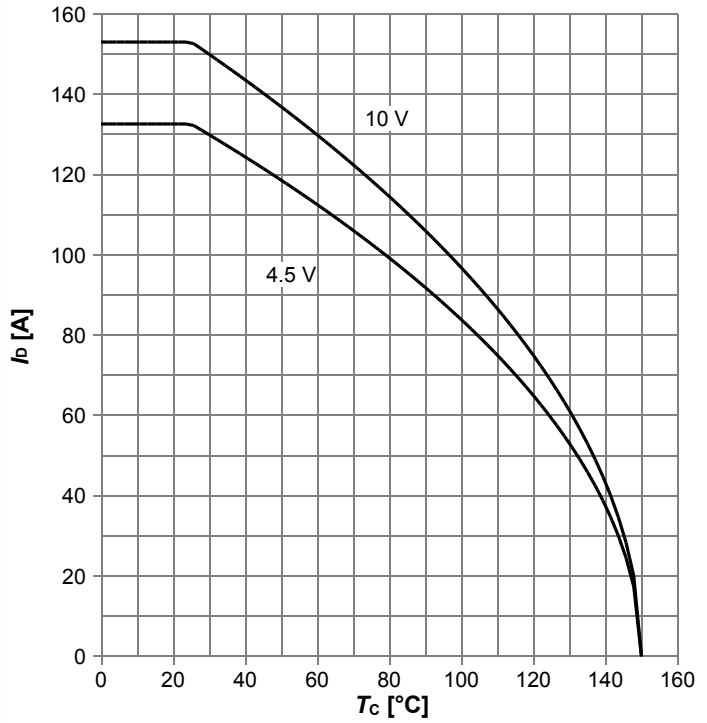
# 4 Electrical characteristics diagrams

**Diagram 1: Power dissipation**



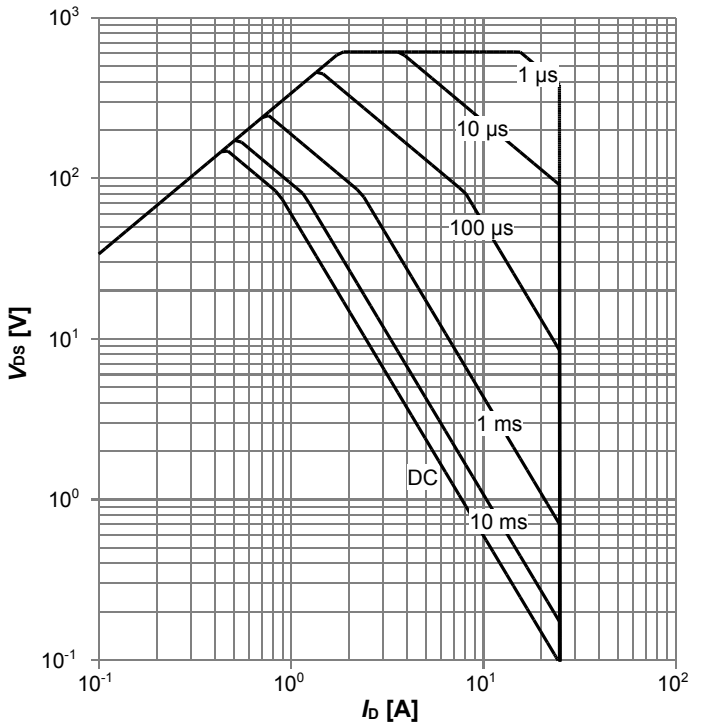

$P_{tot}$=f($T_C$)

**Diagram 2: Drain current**



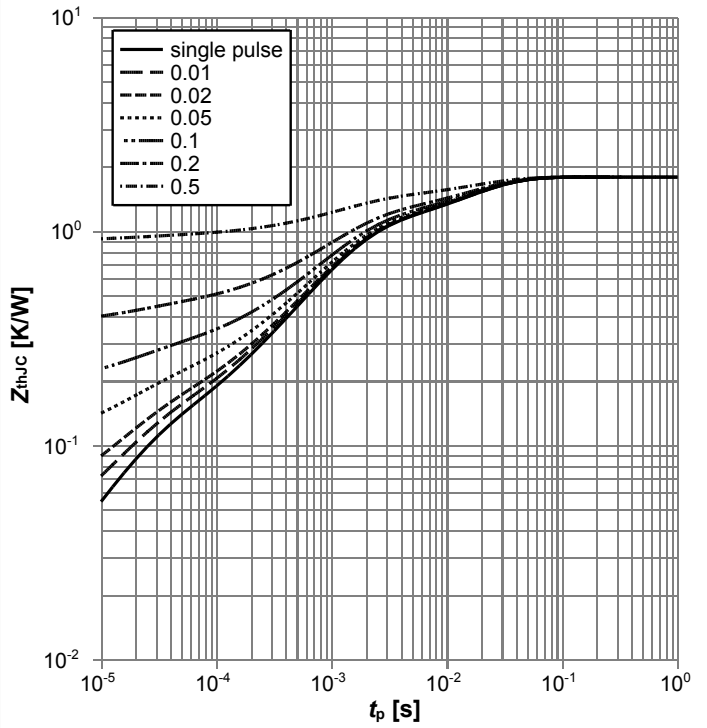

$I_D$=f($T_C$); parameter: $V_{GS}$

**Diagram 3: Safe operating area**



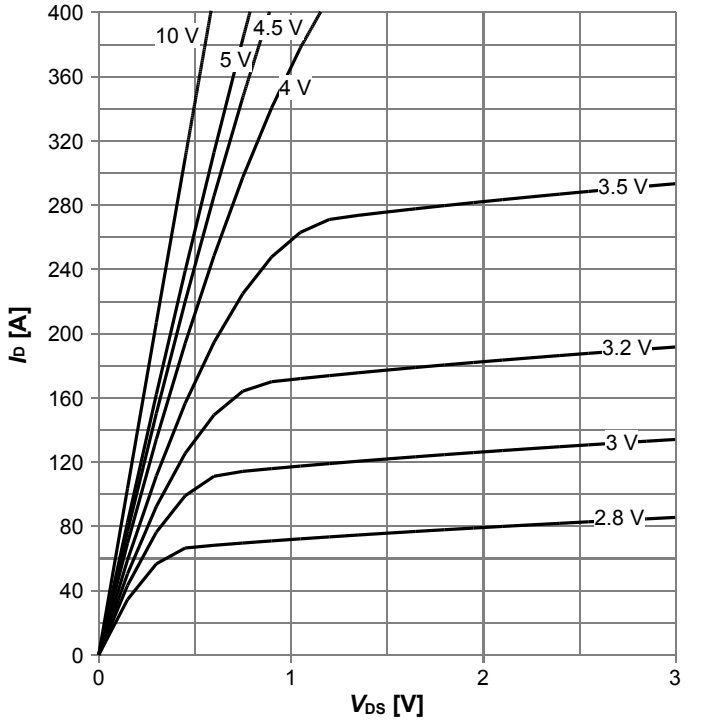

$I_D$=f($V_{DS}$); $T_C$=25 °C; $D$=0; parameter: $t_p$

**Diagram 4: Max. transient thermal impedance**



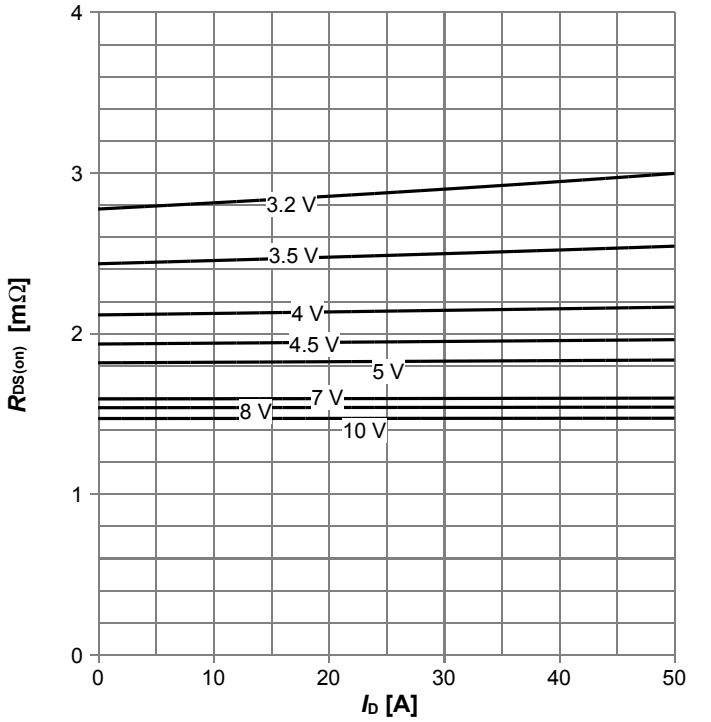

$Z_{thJC}$=f($t_p$); parameter: $D$=$t_p$/$T$

**Diagram 5: Typ. output characteristics**



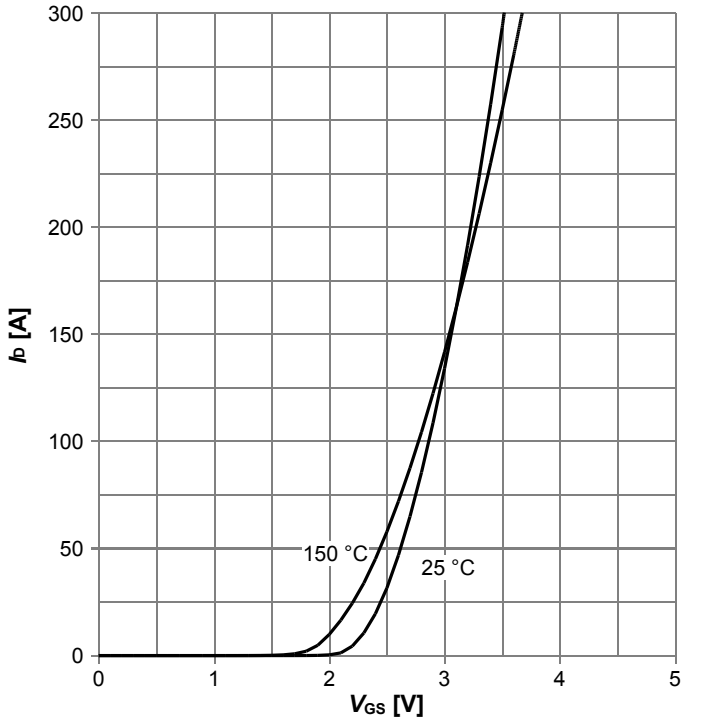

$I_D$=f($V_{DS}$); $T_j$=25 °C; parameter: $V_{GS}$

**Diagram 6: Typ. drain-source on resistance**



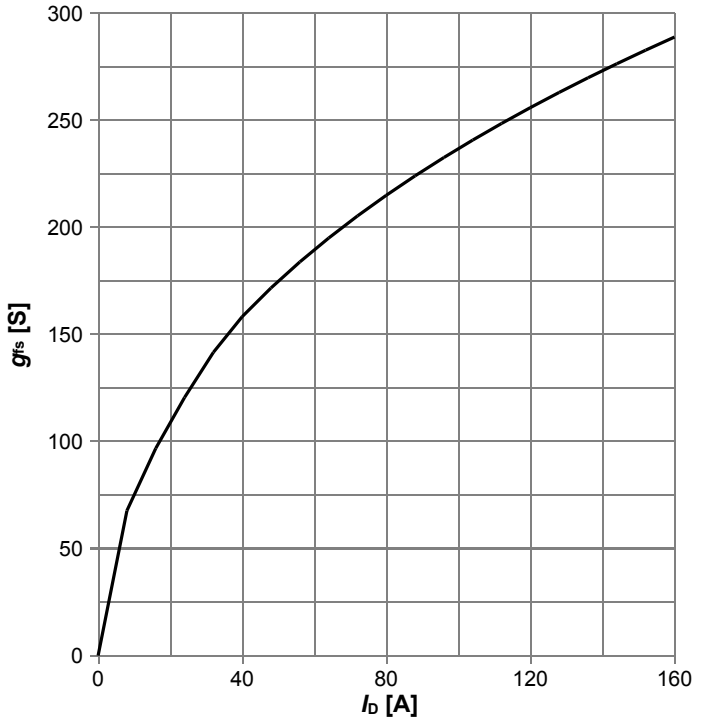

$R_{DS(on)}$=f($I_D$); $T_j$=25 °C; parameter: $V_{GS}$

**Diagram 7: Typ. transfer characteristics**



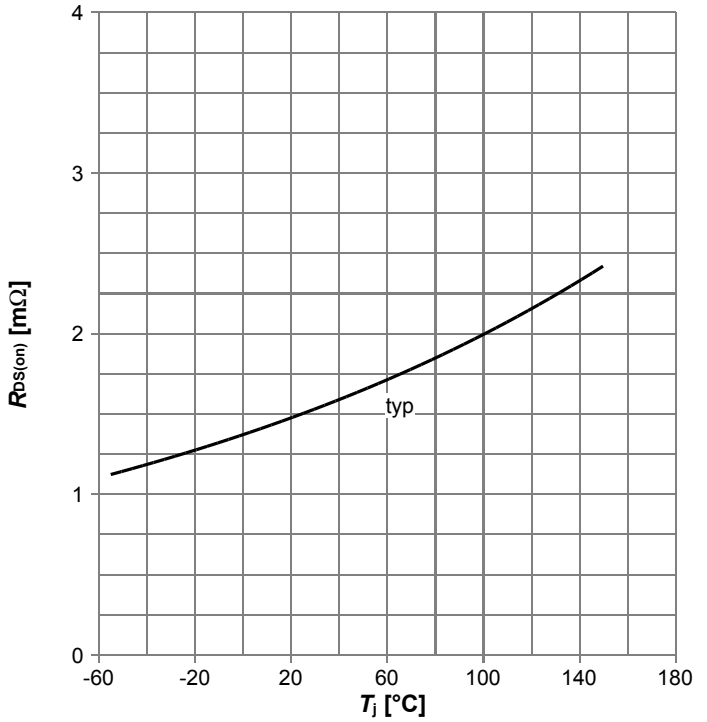

$I_D$=f($V_{GS}$); |$V_{DS}$|>2|$I_D$|$R_{DS(on)max}$; parameter: $T_j$

**Diagram 8: Typ. forward transconductance**



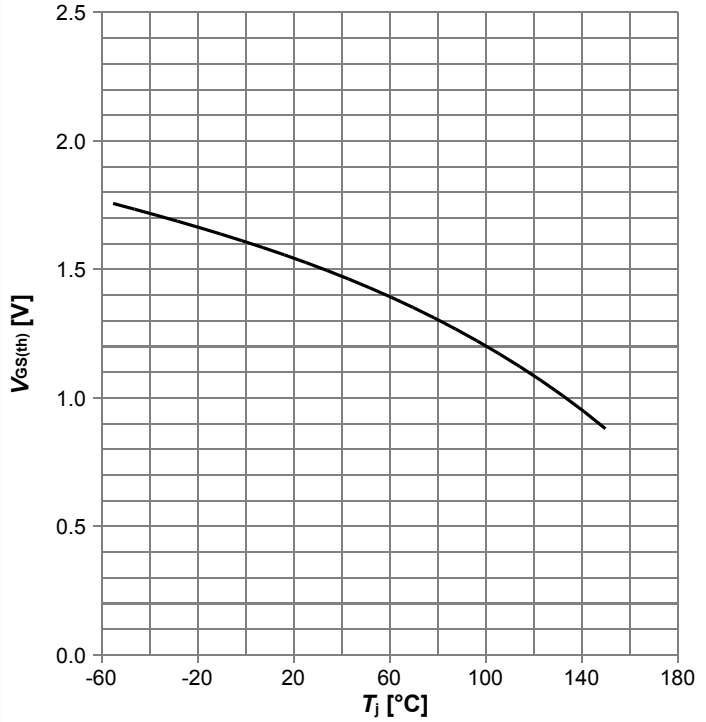

$g_{fs}$=f($I_D$); $T_j$=25 °C

**Diagram 9: Drain-source on-state resistance**



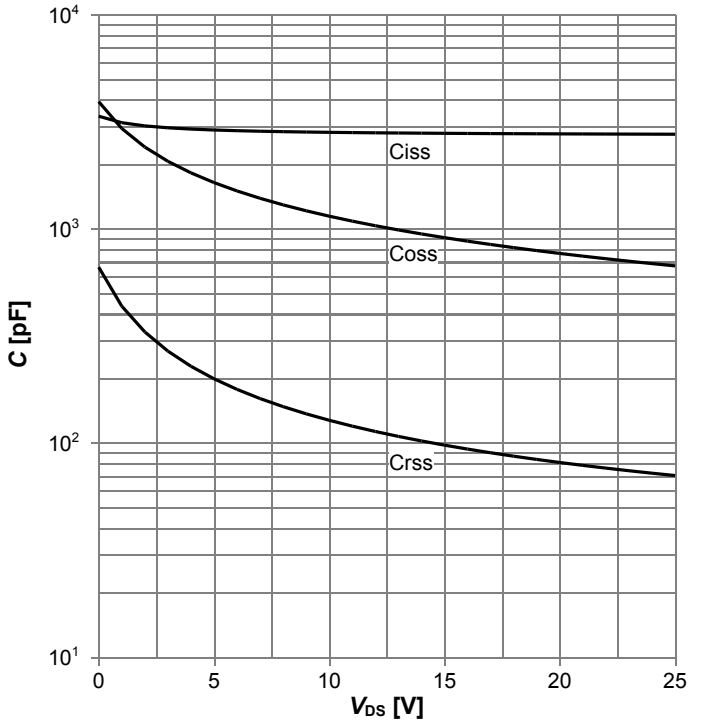

$R_{DS(on)}$=f($T_j$); $I_D$=30 A; $V_{GS}$=10 V

**Diagram 10: Typ. gate threshold voltage**



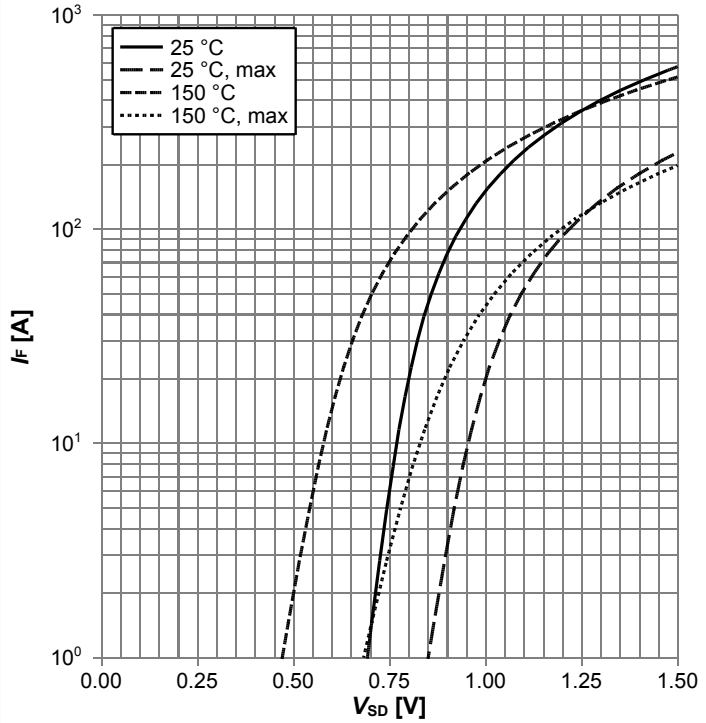

$V_{GS(th)}$=f($T_j$); $V_{GS}$=$V_{DS}$; $I_D$=250 µA

**Diagram 11: Typ. capacitances**



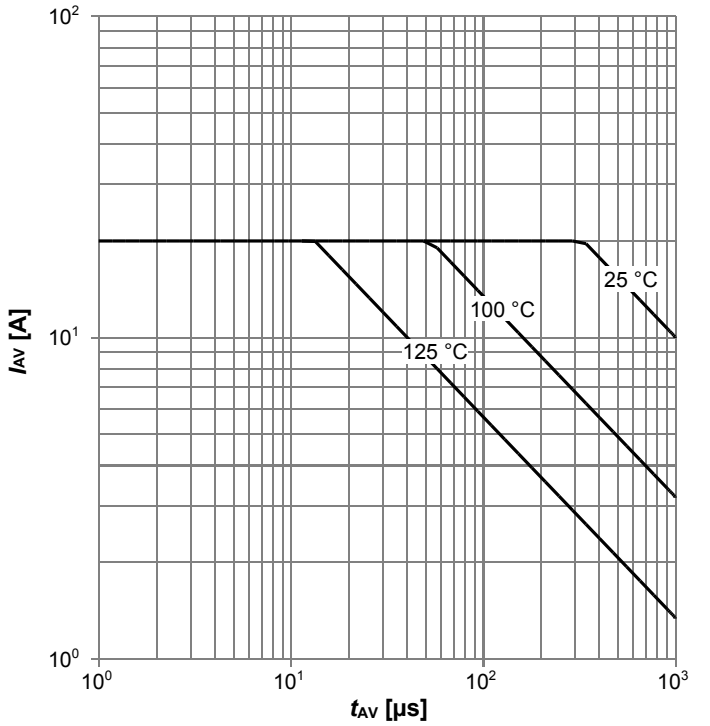

$C$=f($V_{DS}$); $V_{GS}$=0 V; $f$=1 MHz

**Diagram 12: Forward characteristics of reverse diode**



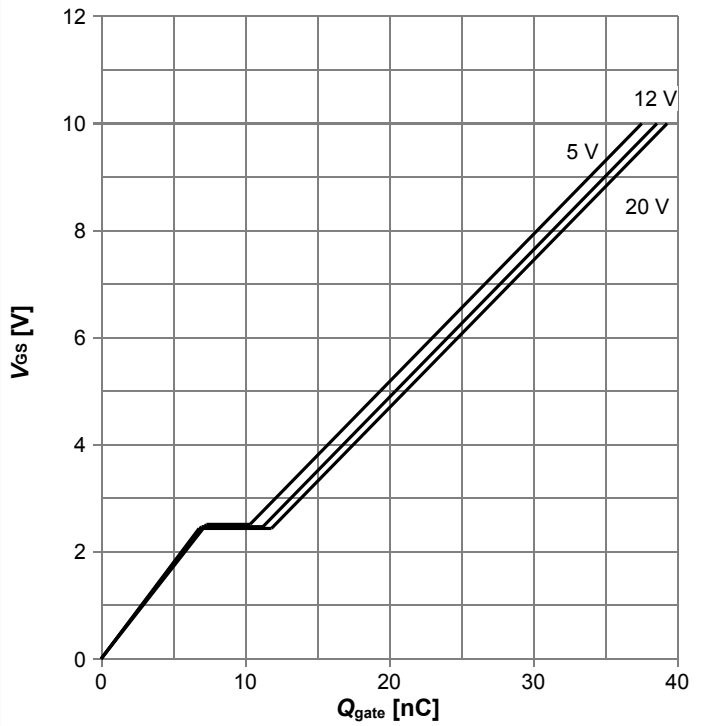

$I_F$=f($V_{SD}$); parameter: $T_j$

**Diagram 13: Avalanche characteristics**



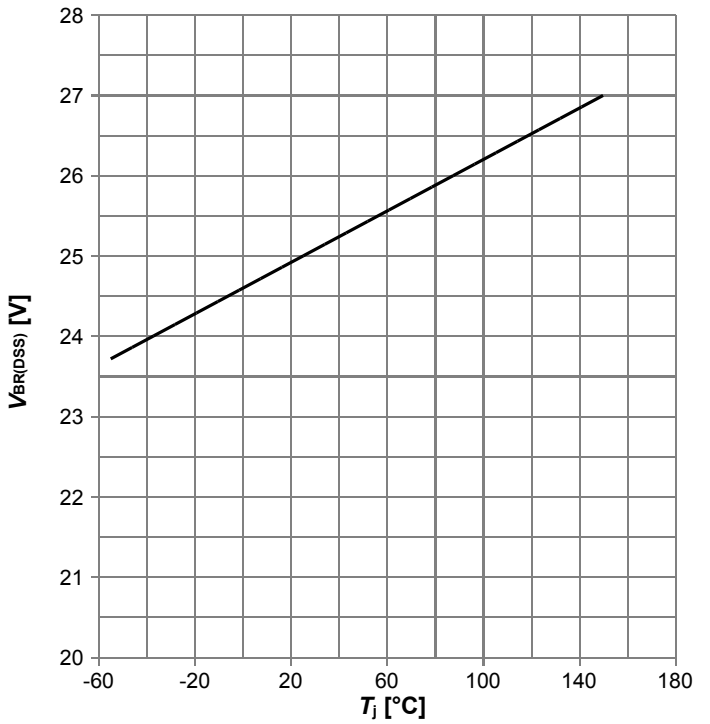

$I_{AS}$=f($t_{AV}$); $R_{GS}$=25 Ω; parameter: $T_{j(start)}$

**Diagram 14: Typ. gate charge**



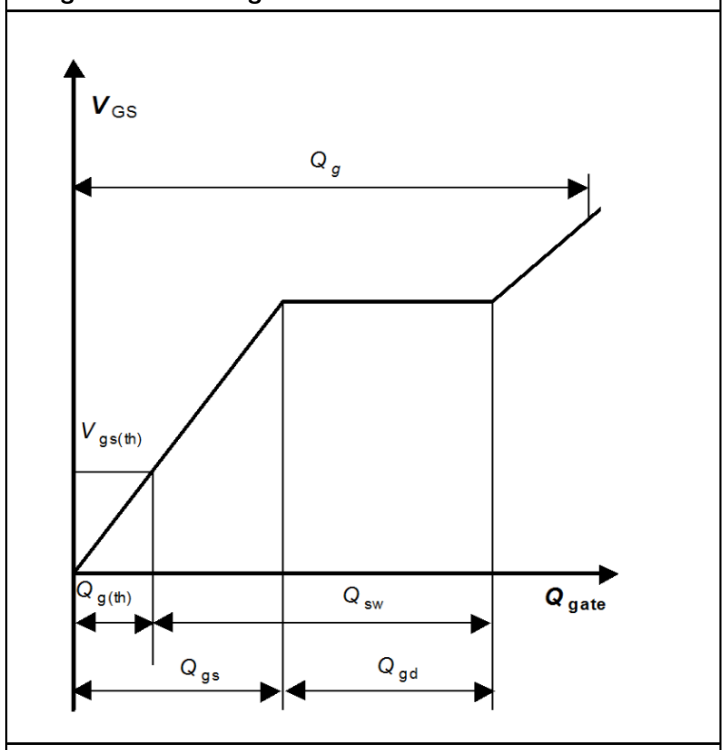

$V_{GS}$=f($Q_{gate}$); $I_D$=30 A pulsed; parameter: $V_{DD}$

**Diagram 15: Drain-source breakdown voltage**

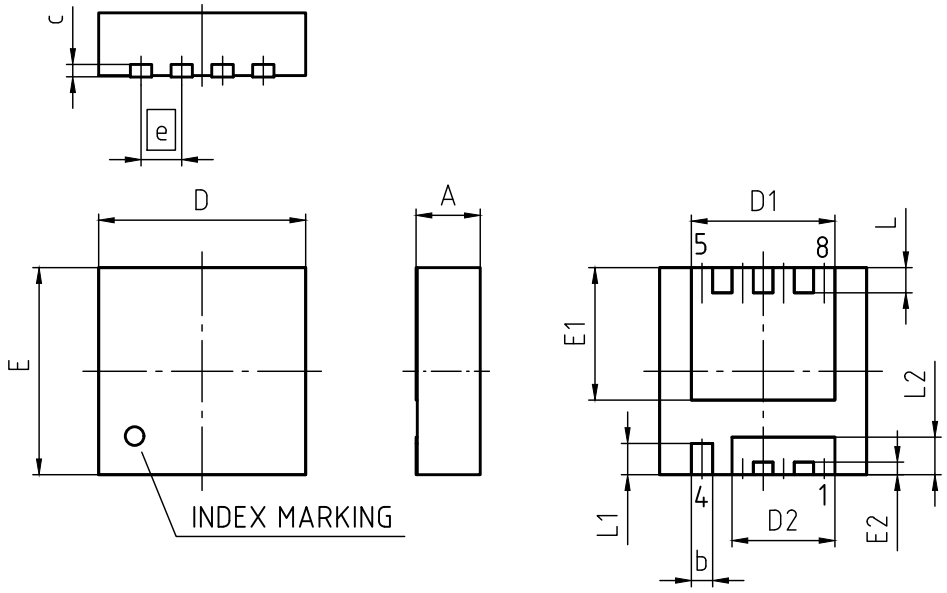



$V_{BR(DSS)}$=f($T_j$); $I_D$=1 mA

**Diagram Gate charge waveforms**



# 5 Package Outlines




| PACKAGE - GROUP NUMBER: | PG-TSDSON-8-U03 | |
|---|---|---|
| REVISION: 03 | DATE: 20.10.2020 | |
| DIMENSIONS | MILLIMETERS | |
| | MIN. | MAX. |
| A | 0.90 | 1.10 |
| b | 0.24 | 0.44 |
| c | (0.20) | |
| D | 3.20 | 3.40 |
| D1 | 2.19 | 2.39 |
| D2 | 1.54 | 1.74 |
| E | 3.20 | 3.40 |
| E1 | 2.01 | 2.21 |
| E2 | 0.10 | 0.30 |
| e | 0.65 | |
| L | 0.30 | 0.50 |
| L1 | 0.40 | 0.60 |
| L2 | 0.50 | 0.70 |
| aaa | 0.06 | |

**Figure 1 Outline PG-TSDSON-8 FL, dimensions in mm**

## Revision History

BSZ018NE2LS

**Revision: 2020-11-13, Rev. 2.4**

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|---|---|---|
| 2.3 | 2020-08-11 | Update current rating and footnotes |
| 2.4 | 2020-11-13 | Update package drawing |

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